

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 4, line 1 with the following amended paragraph:

A method for fabricating a CMOS image sensor comprising low voltage buried photodiode and transfer transistor is disclosed. ~~the~~ The disclosed method comprises: forming a field oxide for defining active area and field area on certain area of an epitaxial layer formed on a substrate, and forming a gate of transfer transistor on the epitaxial layer of the active area; forming the low voltage buried photodiode doping region in alignment with one side of the gate of transfer transistor and field oxide; forming a spacer insulation layer by stacking layers of oxide and nitride over the whole structure; forming a spacer block mask to open areas excluding doping region for the low voltage buried photodiode; and removing the spacer block mask, and forming a floating diffusion region on other side of the transfer transistor.